(11) Publication number:

**0 072 209** A3

12)

## **EUROPEAN PATENT APPLICATION**

(21) Application number: 82304139.7

22 Date of filing: 05.08.82

(f) Int. Cl.4: **G 11 C 17/00**, H 01 L 27/10, H 01 L 21/76

30 Priority: 08.08.81 JP 124582/81

7) Applicant: FUJITSU LIMITED, 1015, Kamikodanaka Nakahara-ku, Kawasaki-shi Kanagawa 211 (JP)

43 Date of publication of application: 16.02.83 Bulletin 83/7

② Inventor: Ueno, Kouji, 1360, Shukugawara Tama-ku, Kawasaki-shi Kanagawa 214 (JP)

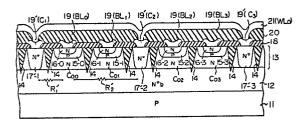
84 Designated Contracting States: DE FR GB

(14) Representative: Rackham, Stephen Neil et al, GILL JENNINGS & EVERY 53-64 Chancery Lane, London WC2A 1HN (GB)

Bate of deferred publication of search report: 12.02.86 Bulletin 86/7

(54) Junction short-circuiting-type programmable read-only memory device.

(5) A junction short-circuiting-type programmable readonly memory (PROM) device comprises a plurality of striped buried layers (12) with a plurality of striped collector regions (13) on them. A plurality of base regions (15-0 to 15-5) are arranged in a row, with one in each of the collector regions, and, in addition, an emitter region (16-0 to 16-5) is arranged in each base region. Further, in each of the collector regions, a plurality of high impurity regions (17'-1 to 17'-3) of the same conductivity type as that of the collector region are formed to connect the collector region to the word lines and each base region is connected to a bit line. One of the high impurity regions are provided for each two base regions which avoids variations in the separation of the memory cells and the collector connections and consequent variations in the write-in current, and, in addition, decreases the resistance between the emitter and collector so that the area of the memory cells can be reduced with a consequent increase in the integration density of the memory device.



EP 0 072 209 A3



## **EUROPEAN SEARCH REPORT**

007,2,2,0,9,

EP 82 30 4139

		IDERED TO BE RELEVAN	<del></del>	
Category		h indication, where appropriate, ant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 3)
D,X		JSHO K.K.)	1,4,5	G 11 C 17/00 H 01 L 27/10 H 01 L 21/76
A	4, no. 137 (E-27 September 1980;	& JP - A - 55 K.K.) 10-07-1980	2,3	
A	4, no. 83 (E-15) 1980; & JP - A (NIPPON DENKI K	.K.) 16-04-1980	1,4,5	
	* Abstract; figures 4,5 *			TECHNICAL FIELDS SEARCHED (Int. Cl. 3)
				H 01 L G 11 C
	The present search report has be search report has been	Date of त्लागिन्तुगा नृतिह ऋarch		AN DEXAMINES.
do A : teo O : no	rticularly relevant if taken alone rticularly relevant if combined w cument of the same category shnological background n-written disclosure ermediate document	E : earlier pa after the ith another D : documer L : documer	atent document, filing date nt cited in the ap nt cited for other of the same pate	but published on, or